

**39 EDS Members Elected to the IEEE Grade of Fellow
Effective 1 January 2007**

Richard Keith Ahrenkiel

Natl. Renewable Energy Lab., Golden, CO, USA

For contributions to measurement of minority carrier lifetimes in semiconductor materials

Barry E. Burke

MIT Lincoln Laboratory, Lexington, MA, USA

For contributions to the technology development of charge-coupled devices for imaging and signal processing.

Sethumadhavan Chandrasekhar

Lucent Technologies, Holmdel, NJ, USA

For contributions to the design and development of 1.55 μm opto-electronic integrated circuits for wide-spectrum application in optical communications.

Ih-Chin Chen

Worldwide Semiconductor Manufacturing, Hsin-Chu City, Taiwan

For leadership in the development of advanced CMOS technologies.

John D. Cressler

Auburn University, Auburn, AL, USA

For contributions to the understanding and optimization of silicon and silicon-germanium bipolar transistors.

Sorin Cristoloveanu

Natl. Center for Scientific Research, Grenoble, France

For contributions to Silicon-on-Insulator device physics, technology, and characterization.

Rik W.A.A. de Doncker

Aachen University of Technology, Aachen, Germany

For contributions to the development of high-power resonant soft-switching converters and high-performance digital control of induction machines.

Sang H. Dhong

IBM Austin Research Laboratory, Austin, TX, USA

For contribution to high speed processor and memory chip design.

Samir M. El-Ghazaly

Arizona State University, Tempe, AZ, USA

For contributions to the analysis and simulations of microwave devices and circuits.

Arthur Charles Gossard

Univ. of California, Santa Barbara, Santa Barbara, CA, USA

For contributions to semiconductor microstructure fabrication.

Aditya Kumar Gupta

Northrop Grumman Corporation, Linthicum, MD, USA

For contributions to the advancement of microwave monolithic integrated circuit technology and leadership in the development of manufacturable processes.

Yoshiaki Daimon Hagiwara

Sony Corporation, Tokyo, Japan

For pioneering work on, and development of, solid-state imagers.

Takeo Hattori

Musashi Institute of Technology, Tokyo, Japan

For his contributions to the studies on the formation and the characterization of ultrathin gate oxides for ULSI devices.

James N. Hollenhorst

Agilent Laboratories, Palo Alto, CA, USA

For contributions to ultra-high performance avalanche photodiodes.

Wei Hwang

IBM T.J. Watson Research Center, Yorktown Heights, NY, USA

For contributions to high density cell technology and high speed Dynamic Random Access Memory design.

Hiroshi Ishiwara

Tokyo Institute of Technology, Yokohama, Japan

For contributions to Si-based heterostructure devices and ferroelectric memories.

Dieter Stefan Jager

Gerhard-Mercator-Universitat Duisburg, Duisburg, Germany

For contributions to the development of device concepts in microwaves and photonics.

Robert Forrest Kwasnick

General Electric Medical Systems, Santa Clara, CA, USA

For contributions to the development of amorphous silicon flat panel x-ray imager technology.

Kei May Lau

Hong Kong University of Science & Tech., Kowloon, Hong Kong

For contributions to III-V compound semiconductor heterostructure materials and devices.

Chin Chung Lee

University of California, Irvine, CA, USA

For pioneering research in fluxless bonding technology and contributions to thermal design tools for electronic devices and packages.

Baruch Levush

Naval Research Laboratory, Washington, DC, USA

For leadership in the development of theoretical and computational models of free electron radiation sources.

Bernard S. Meyerson

IBM T.J. Watson Research Center, Yorktown Heights, NY, USA

For the invention of ultra high vacuum chemical vapor deposition and its application to low temperature epitaxy of SiGe for the fabrication of heterojunction bipolar integrated circuits for telecommunications.

Akihiko Morino

NEC Corporation, Kanagawa, Japan

For contributions to the development of System-on-a-Chip for multimedia applications.

Kenji Nishi

Semiconductor Leading Edge Technologies, Inc., Kanagawa, Japan

For contributions to semiconductor process and device modeling and the development of software for their simulation.

Jon Harris Orloff

University of Maryland, College Park, MD, USA

For contributions to Focussed Ion Beam Technology.

Stephen John Pearton

University of Florida, Gainesville, FL, USA

For development of advanced semiconductor processing techniques and their application to compound semiconductor devices.

John Xavier Przybysz

Northrop Grumman Corporation, Baltimore, MD, USA

For contributions in the development and application of Josephson digital circuits to electronic systems, especially radars, communication satellites and data switching networks.

Hans-Martin Rein

Ruhr-University, Bochum, Bochum, Germany

For contributions to the design of high-speed silicon and silicon/germanium bipolar circuits, especially as applied to fiber-optic systems.

Edward Anthony Rezek

TRW, Inc., Redondo Beach, CA, USA

For contributions to GaAs and InP monolithic microwave integrated circuits and optoelectronic devices.

Arvind Kumar Sharma

TRW, Inc., Redondo Beach, CA, USA

For contributions to active device and passive component modeling, and design of high power monolithic millimeter-wave integrated circuits.

Krishna Shenai

University of Illinois, Chicago, Chicago, IL, USA

For contributions to the understanding, development and application of power semiconductor devices and circuits.

Ritu Shrivastava

Alliance Semiconductor Corporation, Santa Clara, CA, USA
For contributions to high performance CMOS memory technology and product development.

James C. Sturm

Princeton University, Princeton, NJ, USA
For contributions to novel silicon-based semiconductor devices, large-area electronics, and engineering education.

Peter Vettiger

IBM Zurich Research Laboratory, Rueschlikon, Switzerland
For contributions to, and leadership in, the development of microfabrication processes for electronic, optoelectronic, and microelectromechanical devices, circuits, and systems.

Yang Yuan Wang

Peking University, Beijing, China
For leadership in China's semiconductor research and education

Isamu Washizuka

Sharp Corporation, Nara, Japan
For contributions to the technology and applications of liquid crystal displays.

Andrew B. Wittkower

Soitec USA Inc., Peabody, MA, USA
For contributions and leadership in the development and advancement of ion implantation techniques, equipment and companies.

Hon-Sum Philip Wong

IBM T.J. Watson Research Center, Yorktown Heights, NY, USA
For contributions to solid-state image sensors and nanoscale CMOS devices.

Max Neil Yoder

Office of Naval Research, Arlington, VA, USA
For leadership of government sponsored development of microwave integrated circuits

The Nominations of the Following IEEE Members Were Evaluated by EDS But the individuals are Not Current Members of EDS

Karl W. Boer

Solar Knoll, Kennett Square, PA, USA
For contributions to research, development, and commercialization of thin film solar cells.

Satoshi Hiyamizu

Osaka University, Osaka, Japan
For contributions to the realization of the first high electron mobility transistor (HEMT).